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10/057,674

Atty. Docket No.  
AM-2602.C1

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(Use several sheets if necessary)



*[Handwritten scribble]*

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Jeng H. Hwang et al.  
Applicants

January 24, 2002  
Filing Date

Unknown  
Group 1754

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U. S. PATENT DOCUMENTS

Examiner Initial	Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate
<i>AB</i>	4,889,588	12/26/89	Fior	156	643	
	4,902,377	02/20/90	Berglund et al.	156	643	
	5,188,704	02/23/93	Babie et al.	156	643	
	5,232,747	08/03/93	Evans Jr.	427	539	
	5,258,093	11/02/93	Maniar	156	626	
	5,492,855	02/20/96	Matsumoto et al.	437	60	
	5,498,768	03/12/96	Nishitani et al.	437	192	
	5,515,984	05/14/96	Yokoyama et al.**	216	41	
	5,527,729	06/28/96	Matsumoto et al.	437	60	
<i>AB</i>	5,554,866	09/10/96	Nishioka et al.	257	295	
<i>AB</i>	5,565,036	10/15/96	Westendorp et al.	118	723	

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*Michael...*

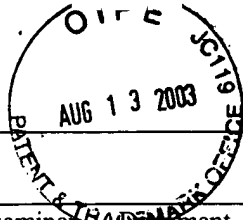
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\* Cited in Search Report in corresponding PCT Application No. PCT/US00/04240.

\*\* Cited by the Examiner during prosecution of parent application, U.S. Serial No. 09/421,467.

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Examiner Initial	Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate
<i>ne</i>	5,658,820	08/19/97	Chung	438	3	
	5,679,213	10/21/97	Noshiro	156	643	
	5,686,339	11/11/97	Lee et al.	437	60	
	5,696,018	12/09/97	Summerfelt et al.	437	60	
	5,702,970	12/30/97	Choi*	437	52	
	5,707,487	01/13/98	Hori et al.	156	659.11	
	5,753,044	02/15/98	Hanawa et al.	118	723	
	5,792,593	08/11/98	McClure et al.	430	314	
	5,854,104	12/29/98	Onishi et al.	438	240	
	6,087,265	07/11/00	Hwang*	438	706	03/13/97
	<del>6,143,476</del>	<del>11/07/00</del>	<del>Ye et al.*</del>	<del>430</del>	<del>318</del>	<del>12/12/97</del>
<i>of</i>	6,277,251	08/21/01	Hwang et al.*	204	192.33	08/26/97
<i>ny</i>	6,482,745	11/19/02	Hwang	438	706	01/13/98

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## FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Publication Date	Name	Class	Subclass	Translation If Appropriate
<i>ny</i>	DE 19728473	01/07/99	Weinrich et al.*	H01L	21/28	Abstract
<i>ny</i>	EP 0725430	08/07/96	Nagano et al.	H01L	21/3205	

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*Michael G. ...*

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	EP 0786805	07/30/97	Nakagawa et al.	H01L	21/321	
	EP 0795896	09/17/97	Kamisawa et al.	H01L	21/311	
	EP 0858103	12/08/98	Kim et al.	H01L	21/3213	
	EP 0889519	01/07/99	Xing et al.*	H01L	21/8242	
	JP 59016334	01/27/84	Tsukura	H01L	21/302	Abstract
	JP 11111695	04/23/99	Fujitsu Ltd.	H01L	21/3065	Abstract
	WO 9800859	01/08/98	DeOrnellas et al.	H01L	21/302	

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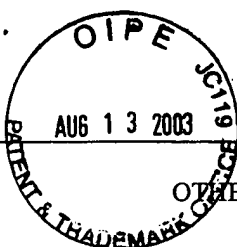
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